

Vishay Siliconix

P-Channel 40-V (D-S) MOSFET

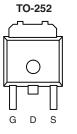
PRODUCT SUMMARY					
V _{DS} (V)	R_{DS(on)} (Ω)	I _D (A)	Q _g (Typ.)		
- 40	0.0081 at V _{GS} = - 10 V	- 50 ^d	60		
- 40	0.0117 at V _{GS} = - 4.5 V	- 48 ^d	00		

FEATURES

- Halogen-free According to IEC 61249-2-21
 Definition
- TrenchFET[®] Power MOSFET
- 100 % $\rm R_{g}$ and UIS Tested
- Compliant to RoHS Directive 2002/95/EC

APPLICATIONS

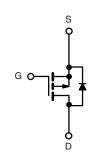
- Power Switch
- · Load Switch in High Current Applications
- DC/DC Converters



Drain Connected to Tab



Ordering Information: SUD50P04-08-GE3 (Lead (Pb)-free and Halogen-free)



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS	S T _C = 25 °C, unless oth	erwise noted		
Parameter		Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	- 40	v	
Gate-Source Voltage		V _{GS}	± 20	v
Continuous Drain Current ($T_{I} = 150 ^{\circ}C$)	T _C = 25 °C	1-	- 50 ^d	
Continuous Drain Current $(1) = 150^{\circ}$ C)	T _C = 70 °C	I _D	- 50 ^d	A
Pulsed Drain Current		I _{DM}	- 100	~ ^
Avalanche Current		I _{AS}	- 46	
Single Avalanche Energy ^a	L = 0.1 mH	E _{AS}	106	mJ
	T _C = 25 °C	P	73.5 ^b	
Maximum Power Dissipation ^a	T _A = 25 °C ^c	– P _D –	2.5	W
Operating Junction and Storage Temperature Ra	ange	T _J , T _{stg}	- 55 to 150	°C

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Limit	Unit		
Junction-to-Ambient (PCB Mount) ^c	R _{thJA}	50	°C/W		
Junction-to-Case (Drain)	R _{thJC}	1.7	0/10		

Notes:

a. Duty cycle \leq 1 %.

b. See SOA curve for voltage derating.

c. When Mounted on 1" square PCB (FR-4 material).

d. Package limited.

COMPLIANT

HALOGEN

SUD50P04-08

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Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static		· · · ·		•			
Drain-Source Breakdown Voltage	V _{DS}	V _{DS} V _{DS} = 0 V, I _D = - 250 μA - 40				V	
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = -250 \ \mu A$	- 1		- 2.5	v	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 20 V$			± 250	nA	
		$V_{DS} = -40 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$			- 1		
Zero Gate Voltage Drain Current	I _{DSS}	V_{DS} = - 40 V, V_{GS} = 0 V, T_{J} = 125 °C			- 50	μA	
		$V_{DS} = -40 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 150 \text{ °C}$			- 250		
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \le$ - 10 V, V_{GS} = - 10 V	- 50			А	
	D	V _{GS} = - 10 V, I _D = - 22 A		0.0067	0.0081		
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 4.5 V, I _D = - 19 A		0.0097	0.0117	Ω	
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 15 V, I _D = - 22 A		45		S	
Dynamic ^b		· · · ·					
Input Capacitance	C _{iss}	V _{GS} = 0 V, V _{DS} = - 20 V, f = 1 MHz		5380		pF	
Output Capacitance	C _{oss}			570			
Reverse Transfer Capacitance	C _{rss}			500			
Tatal Cata Charge	Qg	$V_{DS} = -20 \text{ V}, V_{GS} = -10 \text{ V}, I_{D} = -20 \text{ A}$		106	159	nC	
Total Gate Charge ^c				60	90		
Gate-Source Charge ^c	Q _{gs}	$V_{DS} = -20 \text{ V}, V_{GS} = -4.5 \text{ V}, I_{D} = -20 \text{ A}$		22			
Gate-Drain Charge ^c	Q _{gd}			27			
Gate Resistance	Rg	f = 1 MHz	0.4	1.8	3.6	Ω	
Turn-On Delay Time ^c	t _{d(on)}			15	23		
Rise Time ^c	t _r	V_{DD} = - 20 V, R_L = 2 Ω		12	18	20	
Turn-Off Delay Time ^c	t _{d(off)}	$\rm I_D \cong$ - 10 A, $\rm V_{GEN}$ = - 10 V, $\rm R_g$ = 1 Ω		70	105	- ns	
Fall Time ^c	t _f			18	27		
Drain-Source Body Diode Ratings a	nd Characteri	stics T _C = 25 °C ^b					
Continuous Current	۱ _S				- 50	٨	
Pulsed Current	I _{SM}				- 100	A	
Forward Voltage ^a	V _{SD}	I _F = - 10 A, V _{GS} = 0 V		- 0.8	- 1.5	V	
Reverse Recovery Time	t _{rr}			35	53	ns	
Peak Reverse Recovery Current	I _{RM(REC)}	I _F = - 10 A, dl/dt = 100 A/μs		- 2	- 3	А	
Reverse Recovery Charge	Q _{rr}	1 1		33	50	nC	

Notes:

a. Pulse test; pulse width \leq 300 $\mu s,$ duty cycle \leq 2 %.

b. Guaranteed by design, not subject to production testing.

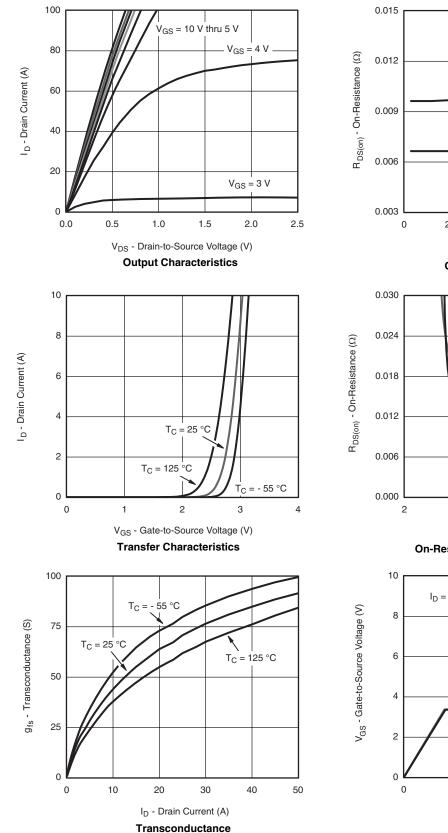
c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

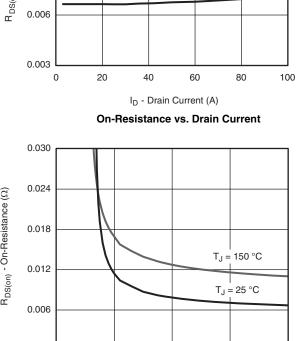


SUD50P04-08

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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



V_{GS} = 4.5 V

V_{GS} = 10 V

 V_{GS} - Gate-to-Source Voltage (V)

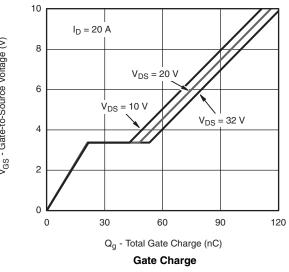
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10

6

4

On-Resistance vs. Gate-to-Source Voltage



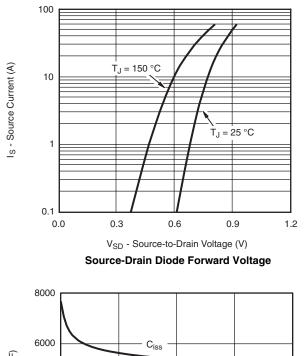
Document Number: 65594 S10-0034-Rev. A, 11-Jan-10

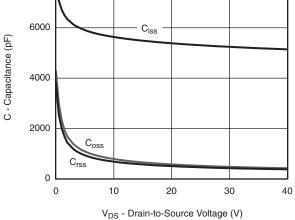
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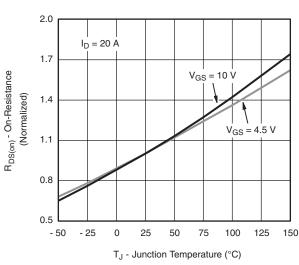
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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

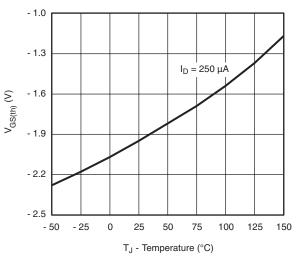




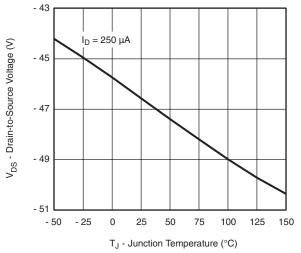
Capacitance



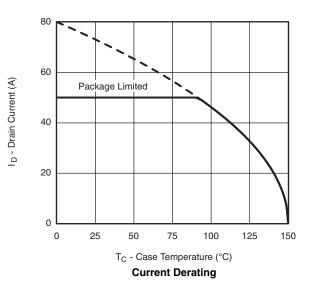


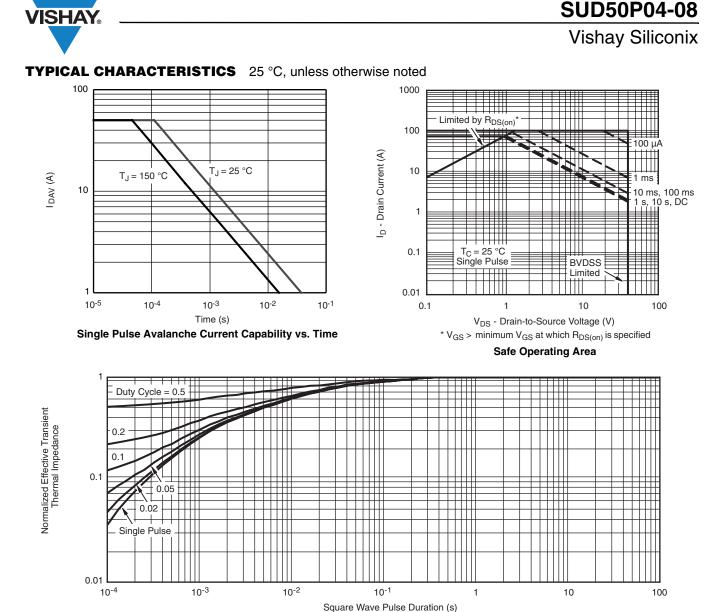


Threshold Voltage



Drain Source Breakdown vs. Junction Temperature



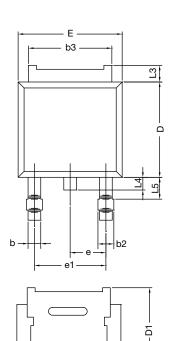


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Normalized Thermal Transient Impedance, Junction-to-Case







E1

TO-252AA Case Outline

	MILLIMETERS		INCHES		
DIM.	MIN.	MAX.	MIN.	MAX.	
А	2.18	2.38	0.086	0.094	
A1	-	0.127	-	0.005	
b	0.64	0.88	0.025	0.035	
b2	0.76	1.14	0.030	0.045	
b3	4.95	5.46	0.195	0.215	
С	0.46	0.61	0.018	0.024	
C2	0.46	0.89	0.018	0.035	
D	5.97	6.22	0.235	0.245	
D1	4.10	-	0.161	-	
E	6.35	6.73	0.250	0.265	
E1	4.32	-	0.170	-	
Н	9.40	10.41	0.370	0.410	
е	2.28 BSC		0.090 BSC		
e1	4.56 BSC		0.180 BSC		
L	1.40	1.78	0.055	0.070	
L3	0.89	1.27	0.035	0.050	
L4	-	1.02	-	0.040	
L5	1.01	1.52	0.040	0.060	
ECN: T13-0359-Rev. O, 03-Jun-13 DWG: 5347					

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Notes

• Dimension L3 is for reference only.

• Xi'an, Mingxin, and GEM SH actual photo.



Revision: 03-Jun-13

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1



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RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads Dimensions in Inches/(mm)

Return to Index



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